

ZK2500-RECTIFIER DIODE

Jiangsu Yangjie Runau Semiconductor Co.,Ltd

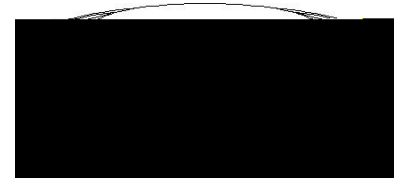
2000-3000 V_{RRM}

FAST RECOVERY RECTIFIER DIODE

Features:

ZT80cT

- . All diffused structure
- . High surge rating
- . Blocking capability up to 3000 volts
- . Soft recovery
- . Ceramic housing hermetic package
- . Pressure assembled device



ELECTRICAL CHARACTERISTICS AND RATINGS

Reverse Blocking

V_{RRM} = Repetitive peak reverse voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage current	I _{RRM}	15 mA 80 mA (3)
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Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average forward current	I _{F(AV)}		2500		A	Sinewave 180°, T _c = 70
RMS forward current	I _{FRMS}		3925		A	
Peak one cycle surge (non repetitive) current	I _{FSM}		38000		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j = 125
I square t	I ² t		7220000		A ² s	8.3 msec and 10.0 msec
Peak forward voltage	V _{FM}		2.40		V	I _{FM} = 3000A; Duty cycle 0.01%
Reverse Recovery Current (4)	I _{RM(REC)}		*		A	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max
Reverse Recovery Charge (4)	Q _{rr}		*		μC	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max
Reverse Recovery Time (4)	t _{rr}		8		μs	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max

* For guaranteed maximum values, contact factory

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